

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
100V	250mΩ @ V _{GS} = 10V	2.9A
	300mΩ @ V _{GS} = 6V	2.6A

Description and Applications

This new generation trench MOSFET features a unique structure that combines the benefits of low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
 For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

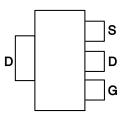
This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
 https://www.diodes.com/quality/product-definitions/

Mechanical Data

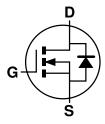
- Package: SOT223 (Type DN)
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)



Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Packing		king
Part Number	Package	Qty.	Carrier
ZXMN10A08GTA	SOT223 (Type DN)	1,000	Tape & Reel

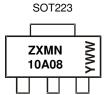
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Unlocate and Antimony free "Green" and defined as these which centre in 2000 nm homine (21500 nm total Br. Cl) and

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



 $\label{eq:2XMN10A08} \begin{array}{l} \mbox{=} \mbox{Product Type Marking Code} \\ \mbox{YWW} \mbox{=} \mbox{Date Code Marking} \\ \mbox{Y or } \overline{Y} \mbox{=} \mbox{Last Digit of Year (ex: 2= 2022)} \\ \mbox{WW or } \overline{WW} \mbox{=} \mbox{Week Code (01~53)} \end{array}$



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (V _{GS} =10V; TA = +25°C) (Note 6)		2.9	
(V _{GS} =10V; TA = +70°C) (Note 6)	I _D	2.3	А
(V _{GS} =10V; TA = +25°C) (Note 5)		2.0	
Pulsed Drain Current (Note 7)	I _{DM}	11	Α
Continuous Source Current (Body Diode) (Note 6)	ls	2.9	A
Pulsed Source Current (Body Diode) (Note 7)	Ism	11	A

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 5) Linear Derating Factor	PD	2.0 16	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear Derating Factor	PD	3.9 31	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	62.5	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	32	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

			1	1	T	1	
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	100	-	-	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	IDSS	-	-	0.5	μA	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	2	-	-	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance (Note 8)	R _{DS(on)}	-	-	0.25 0.30	Ω	$V_{GS} = 10V, I_D = 3.2A$	
Forward Transconductance (Notes 8, 10)		-	5	-	S	V _{GS} = 6V, I _D =2.6A V _{DS} = 15V, I _D =3.2A	
Diode Forward Voltage (Note 8)	VSD	-	0.87	0.95	V	TJ=25°C, IS=3.2A, VGS=0V	
DYNAMIC CHARACTERISTICS (Note 10)	1						
Input Capacitance	C _{iss}	-	405	-	pF		
Output Capacitance	C _{oss}	-	28.2	-	pF	V _{DS} = 50V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	-	14.2	-	pF		
Turn-On Delay Time (Note 9)	t _{D(on)}	-	3.4	-	ns	$V_{DD} = 30V, I_D = 1.2A, V_{GS} = 10V, \label{eq:VDD} R_G = 6\Omega$	
Turn-On Rise Time (Note 9)	t _R	-	2.2	-	ns		
Turn-Off Delay Time (Note 9)	t _{D(off)}	-	8	-	ns		
Turn-Off Fall Time (Note 9)	t _F	-	3.2	-	ns		
Gate Charge (Note 9)	Qg	-	4.2	-	nC	$V_{DS} = 50V, V_{GS} = 5V I_D = 1.2A$	
Total Gate Charge (Note 9)	Qg	-	7.7	-	nC	$V_{DS} = 50V, V_{GS} = 10V I_D = 1.2A$	
Gate-Source Charge (Note 9)	Qgs	-	1.8	-	nC		
Gate-Drain Charge (Note 9)	Qgd	-	2.1	-	nC		
Reverse Recovery Time	trr	-	27	-	ns	-TJ=25°C, Is=1.2A, di/dt= 100A/μs	
Reverse Recovery Charge	Qrr	-	32	-	nC		

5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

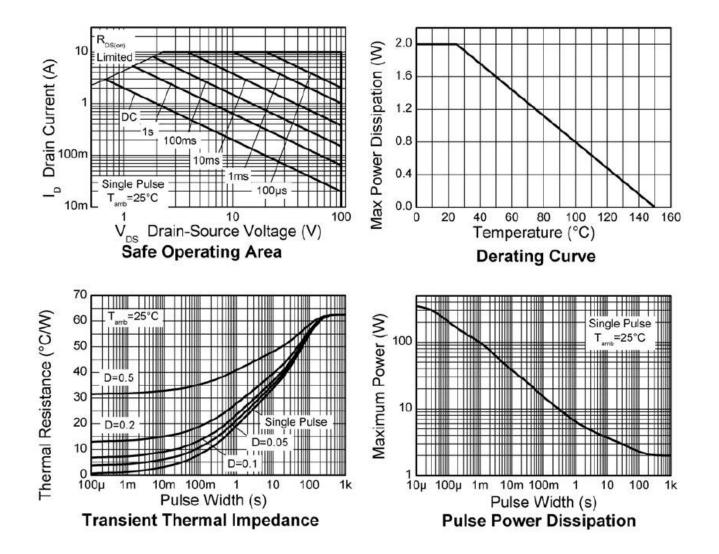
For a device surface mounted on 25mm rA2 PCB with FR4 PCB with fight coverage of single sided 102 copper, in still air conditions.
 For a device surface mounted on FR4 PCB measured at t≦10 secs.
 Repetitive rating - 25mm r 25mm FR4 PCB, D=0.02, pulse width 300µs - pulse width limited by maximum junction temperature.
 Measured under pulsed conditions. Pulse width≦300µs. Duty cycle ≦2%.
 Switching characteristics are independent of operating junction temperature.

10. For design aid only, not subject to production testing.

Notes:

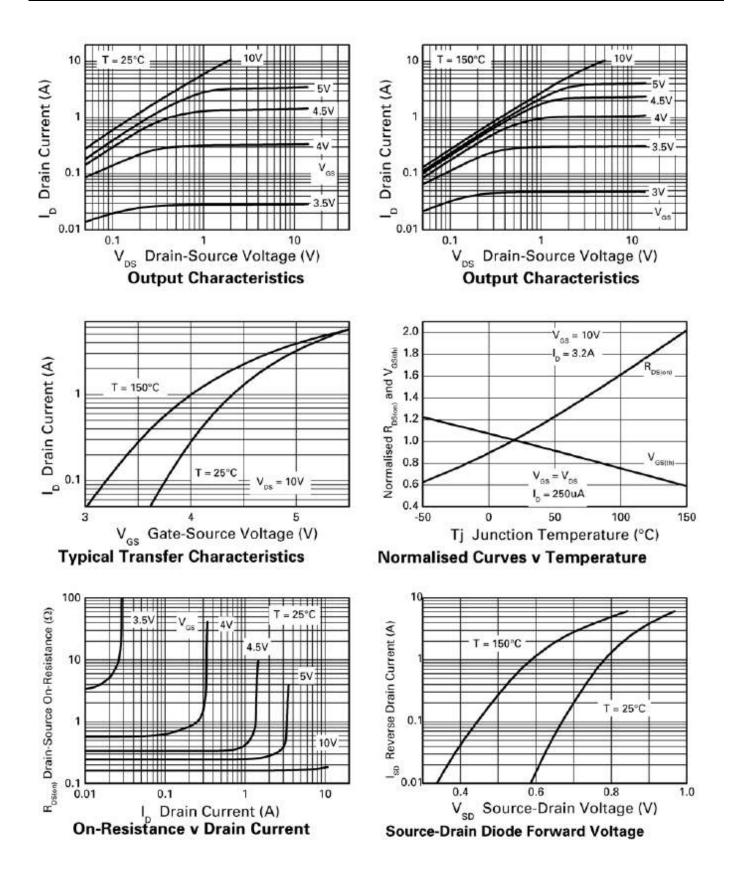


Thermal Characteristics



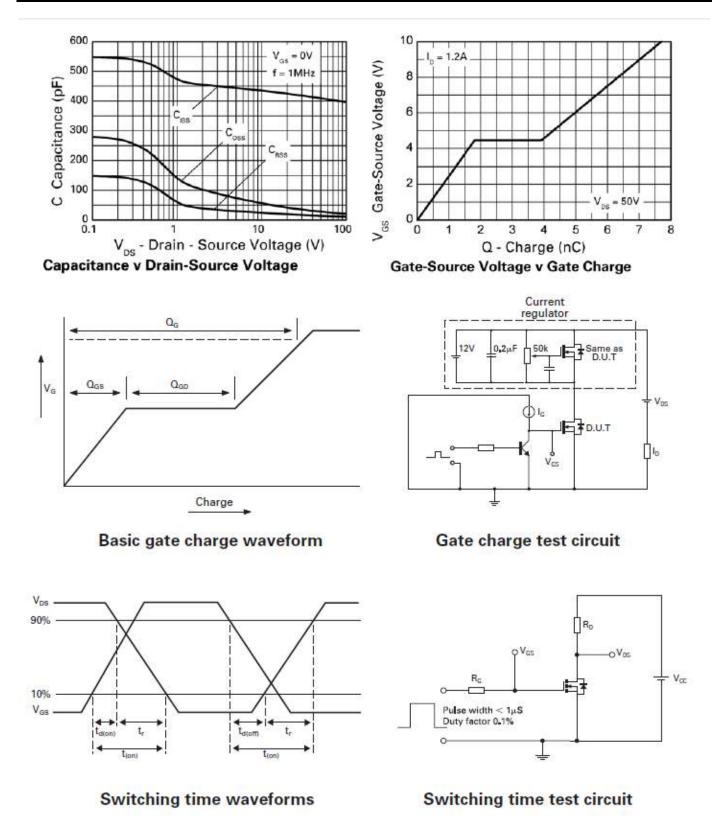


Typical Characteristics





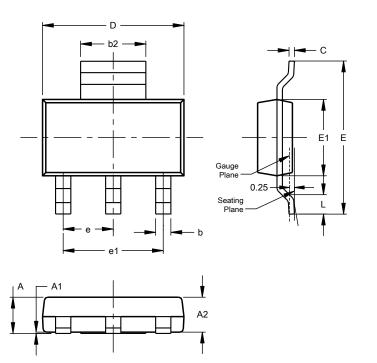
Typical Characteristics (continued)





Package Outline Dimensions

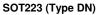
Please see http://www.diodes.com/package-outlines.html for the latest version.



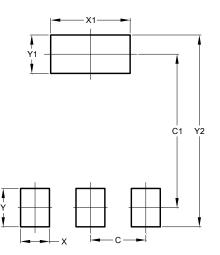
SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α		1.70		
A1	0.01	0.15		
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32		
D	6.30	6.70		
Е	6.70	7.30		
E1	3.30	3.70		
е			2.30	
e1			4.60	
L	0.85			
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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